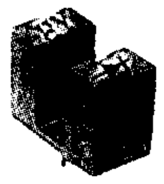
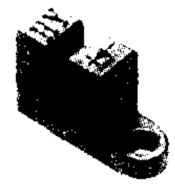
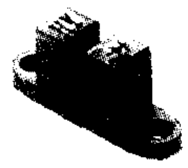
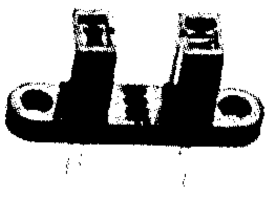
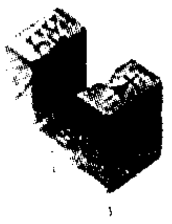
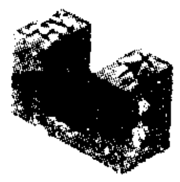
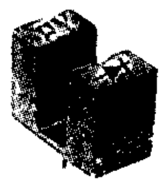
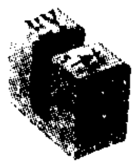
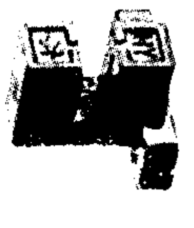
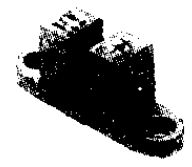
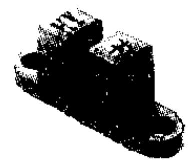
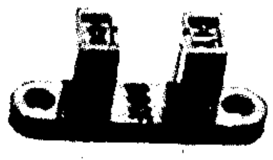
OUTLINE	DEVICE		IREDV$_F$	SENSORV$_{CEO}$	SENSORV$_{CEO}$	ICMIN.	PACKAGE DIMENSION
	槽 距	PARTNO.	TYP. @I$_F$=20mA	MIN. @I$_C$=ImA	MIN. IE=100μA	@I$_F$=20Ma/ V$_{ce}$=5V	
	5.2mm	HY-301A	1.2V	30V	5V	0.5mA	Fig.1-27
	6.0mm	HY-301-05	1.2V	30V	5V	0.5mA	Fig.1-28
	5.0mm	HY-301-07	1.2V	30V	5V	0.4mA	Fig.1-29
	4.1mm	HY-301-19	1.2V	30V	5V	1.5mA	Fig.1-30
	4.0mm	HY-301-21	1.2V	30V	5V	0.4mA	Fig.1-31
	2.7mm	HY-306-01	1.2V	30V	5V	5.0mA	Fig.1-32
	3.0mm	HY-306-02	1.2V	30V	5V	0.5mA	Fig.1-33
	3.2mm	HY870L	1.2V	30V	5V	0.5mA	Fig.1-47
	3.2mm	HY870P	1.2V	30V	5V	0.5mA	Fig.1-48
	3.0mm	HY805	1.2V	30V	5V	0.5mA	Fig.1-34

OUTLINE	DEVICE		IREDV$_F$ TYP. @I$_F$=20mA	SENSORV$_{CEO}$ MIN. @I$_C$=ImA	SENSORV$_{CEO}$ MIN. IE=100μA	ICMIN. @I$_F$=20Ma/ V$_{ce}$=5V	PACKAGE DIMENSION	
	槽 距	PARTNO.						
	3.2mm	HY860C	1.2V	30V	5V	0.5mA	Fig.1-45	
	4.2mm	HY860D	1.2V	30V	5V	0.5mA	Fig.1-46	
	6.0mm	HY860F	1.2V	30V	5V	0.5mA	Fig.1-47	
	8.0mm	HY860H	1.2V	30V	5V	0.5mA	Fig.1-48	
	3.2mm	HY860N	1.2V	30V	5V	0.5mA	Fig.1-49	
	10mm	HY810H	1.2V	30V	5V	O.5mA	Fig.1-50	
		HY308	1.2V	30V	5V	100uA	Fig.1-51	
	IC mA	HY5000/L	CTR %	IF mA	V$_{CEO}$1MA	V$_{CEO}$1V	I$_F$ mA	I$_C$ mA
	>0.3		>1.5	20	>32	<0.3	20	0.1
	IC mA	HY70	CTR %	IF mA	V$_{CEO}$1MA	V$_{CEO}$1V	I$_F$ mA	I$_C$ mA
	>0.3		>1.5	20	>32	<0.3	20	0.1

OUTLINE	DEVICE		IREDV$_F$ TYP. @I$_F$=20mA	SENSORV$_{CEO}$ MIN. @I$_C$=ImA	SENSORV$_{CEO}$ MIN. IE=100μA	ICMIN. @I$_F$=20Ma/ V$_{ce}$=5V	PACKAGE DIMENSION
	槽距	PARTNO.					
	5.2mm	HY-301A	1.2V	30V	5V	0.5mA	Fig.1-27
	6.0mm	HY-301-05	1.2V	30V	5V	0.5mA	Fig.1-28
	5.0mm	HY-301-07	1.2V	30V	5V	0.4mA	Fig.1-29
	4.1mm	HY-301-19	1.2V	30V	5V	1.5mA	Fig.1-30
	4.0mm	HY-301-21	1.2V	30V	5V	0.4mA	Fig.1-31
	2.7mm	HY-306-01	1.2V	30V	5V	5.0mA	Fig.1-32
	3.0mm	HY-306-02	1.2V	30V	5V	0.5mA	Fig.1-33
	3.2mm	HY870L	1.2V	30V	5V	0.5mA	Fig.1-47
	3.2mm	HY870P	1.2V	30V	5V	0.5mA	Fig.1-48
	3.0mm	HY805	1.2V	30V	5V	0.5mA	Fig.1-34

OUTLINE	DEVICE 槽距	DEVICE PARTNO.	IREDV$_F$ TYP. @I$_F$=20mA	SENSORV$_{CEO}$ MIN. @I$_C$=ImA	SENSORV$_{CEO}$ MIN. IE=100μA	ICMIN. @I$_F$=20Ma/ V$_{ce}$=5V	PACKAGE DIMENSION	
	3.2mm	HY860C	1.2V	30V	5V	0.5mA	Fig.1-45	
	4.2mm	HY860D	1.2V	30V	5V	0.5mA	Fig.1-46	
	6.0mm	HY860F	1.2V	30V	5V	0.5mA	Fig.1-47	
	8.0mm	HY860H	1.2V	30V	5V	0.5mA	Fig.1-48	
	3.2mm	HY860N	1.2V	30V	5V	0.5mA	Fig.1-49	
	10mm	HY810H	1.2V	30V	5V	O.5mA	Fig.1-50	
		HY308	1.2V	30V	5V	100uA	Fig.1-51	
	IC mA	HY5000/L	CTR %	IF mA	V_{CEO}1MA	V_{CEO}1V	I$_F$ mA	I$_C$ mA
	>0.3		>1.5	20	>32	<0.3	20	0.1
	IC mA	HY70	CTR %	IF mA	V_{CEO}1MA	V_{CEO}1V	I$_F$ mA	I$_C$ mA
	>0.3		>1.5	20	>32	<0.3	20	0.1

Photointerrupters

Qutline	Device		Gap (mm)	Lead Distance (mm)	Slit Width (mm)	I_C Min. @I_F=20mA/ V_{CE}=5V(mA)	Package Dimension
	Package	Part No.					
	Slotted Type	HY860C	3.2	8.13	1.2	0.8	Fig.11-8
	Slotted Type	HY860D	4.1	8.3	1.2	0.5	Fig.11-9
	Slotted Type	HY860F	6.0	10.45	1.2	0.5	Fig.11-10
	Slotted Type	HY860H	8.0	12.5	1.2	0.4	Fig.11-11
	Slotted Type	HY860N	3.2	8.13	1.2	0.8	Fig.11-12
	Slotted Type	HY870P	3.2	8.13	1.2	0.8	Fig.11-13
	Slotted Type	HY870L	3.2	8.13	1.2	0.8	Fig.11-14
	Slotted Type	HY805	3.0	8.0	1.2	0.5	Fig.11-15

HING YIP ELECTRONIC

Photointerrupters

Outline	Device		Gap (mm)	Lead Distance (mm)	Slit Width (mm)	I_CMin. @I_F=20mA/ V_{CE}=5V(mA)	Package Dimension
	Package	Part No.					
	Slotted Type	HY301A	5.2	9.6	1.2	0.5	Fig.11-1
	Slotted Type	HY301-05	6.0	10.45	1.0	0.5	Fig.11-2
	Slotted Type	HY301-07	5.0	9.0	1.0	0.5	Fig.11-3
	Slotted Type	HY301-19	4.1	8.3	1.2	0.5	Fig.11-4
	Slotted Type	HY301-21	4.0	8.3	1.2	0.5	Fig.11-5
	Slotted Type	HY306-01	2.7	6.7	1.6	4.0	Fig.11-6
	Slotted Type	HY306-02	3.0	9.2	1.0	0.5	Fig.11-7

HING YIP ELECTRONIC

Electrical Optical Characteristics at Ta=25℃

Parameter	Symbol	Part No.	Min.	Typ.	Max.	Unit	Test Condition
Input LED							
Forward Voltage	V_F			1.2	1.6	V	I_F=20mA
Reverse Current	I_R				100	*u* A	V_R=5V
Output phototransistor							
Collector Dark Current	I_{CEO}				100	nA	V_{CE}=10V
Coupler							
Collector-Emitter Saturation Voltage	V_{CE}(sat)	HY301A			0.4	V	Ic=0.25mA,I_F=20mA
		HY301-05			0.4		Ic=0.25mA, I_F=20mA
		HY301-07			0.4		Ic=0.25mA, I_F=20mA
		HY301-19			0.4		Ic=0.25mA, I_F=20mA
		HY301-21			0.4		Ic=0.25mA, I_F=20mA
		HY306-01			0.4		Ic=2.50mA, I_F=20mA
		HY306-02			0.4		Ic=0.25mA, I_F=20mA
		HY860C			0.4		Ic=0.25mA, I_F=20mA
		HY860D			0.4		Ic=0.25mA, I_F=20mA
		HY860F			0.4		Ic=0.25mA, I_F=20mA
		HY860H			0.4		Ic=0.25mA, I_F=20mA
		HY860N			0.4		Ic=0.25mA, I_F=20mA
		HY870P			0.4		Ic=0.25mA, I_F=20mA
		HY870L			0.4		Ic=0.25mA, I_F=20mA
		HY805			0.4		Ic=0.25mA, I_F=20mA
On State Collector Current	Ic(ON)	HY301A	0.5			mA	V_{CE}=5V, I_F=20mA
		HY301-05	0.5				
		HY301-07	0.5				
		HY301-19	0.5				
		HY301-21	0.5				
		HY306-01	4.0				
		HY306-02	0.5				
		HY860C	0.8				
		HY860D	0.5				
		HY860F	0.5				
		HY860H	0.4				
		HY860N	0.8				
		HY870P	0.8				
		HY870L	0.8				
		HY805	0.5				
Response Time Rise Time	tr			3	15	*u* S	V_{CE}=5V, Ic=2mA R_L=100Ω
Fall Time	tf			4	20		

最大、10V

310-7

26

HING YIP ELECTRONIC

Absolute Maximum Rating at Ta=25℃

Parameter		Symbol	Maximum Rating	Unit
Input LED	Continuous Forward Current	I_F	60	mA
	Reverse Voltage	V_R	5	V
	Peak Forward Current (Pulse Wide=10 S,300pps)	I_{CP}	1	A
	Power Dissipation	P_D	75	mW
Output Phototransistor	Collector Current	I_C	20	mA
	Power Dissipation	P_C	100	mW
	Collector-emitter Voltage	V_{CEO}	30	V
	Emitter-collector Voltage	V_{ECO}	5	V
Operating Temperature Range		Topr	-25℃ to +85 ℃	
Storage Temperature Range		Tstg	-40℃ to +100℃	
Lead Soldering Temperature [1.6mm(.063 in.)from body]		Ts	260℃ for 5 Seconds	